FAIRCHILD SEMICONDUCTOR™

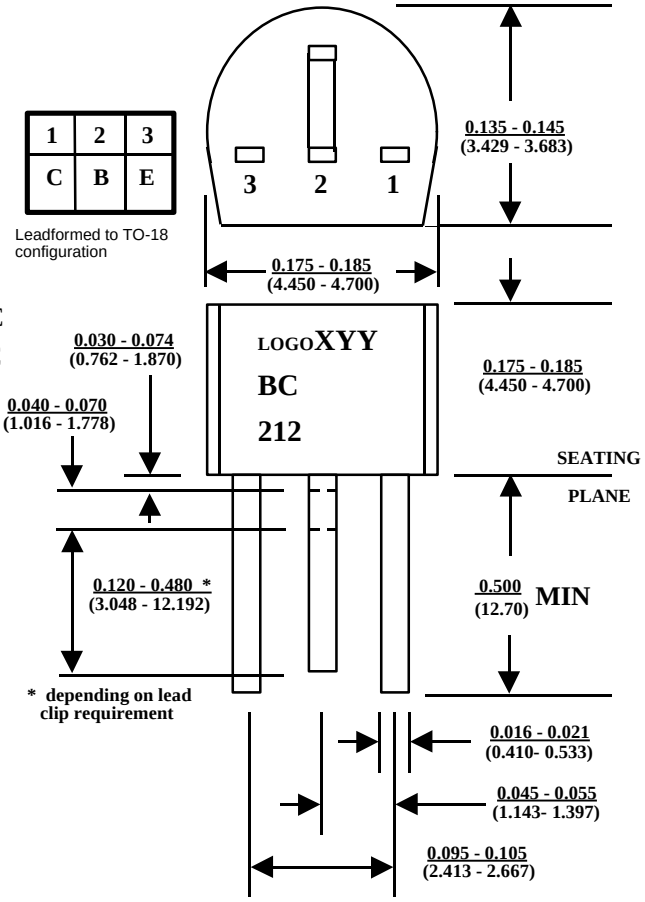
DISCRETE POWER & SIGNAL TECHNOLOGIES

BC212

SILICON PNP SMALL SIGNAL TRANSISTOR

BV_{CEO} . . . . 50V (Min)

h_{FE} . . . . . 60 (Min) @ V_{CE}=5V, I_C= 2mA



ABSOLUTE MAXIMUM RATINGS (NOTE 1)

TEMPERATURES

Storage Temperature	-55 Degrees C to 150 Degrees C
Operating Junction Temperature	150 Degrees C

POWER DISSIPATION (NOTES 2 & 3)

Total Device Dissipation at Ta = 25 Deg C	600 mW

VOLTAGES & CURRENT

V_{CEO}	Collector to Emitter	50V
V_{EBO}	Emitter to Base	5V
I_C	Collector Current	500 mA

ELECTRICAL CHARACTERISTICS (25 Degrees C Ambient Temperature unless otherwise stated)

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
BV_{CBO}	Collector to Base Voltage	60		V	I_C = 10 uA
BV_{CEO}	Collector to Emitter Voltage	50		V	I_C = 2 mA
BV_{EBO}	Emitter to Base Voltage	5		V	I_E = 10 uA
I_{CBO}	Collector Cutoff Current		15	nA	V_{CB} = 30 V
I_{EBO}	Emitter Cutoff Current		15	nA	V_{EB} = 4 V
h_{FE}	DC Current Gain	40 60			V_{CE} =5 V, I_C = 10 uA V_{CE} =5 V, I_C = 2 mA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		0.6	V	I_C = 100 mA I_B = 5 mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		1.4	V	I_C = 100 mA I_B = 5 mA
$V_{BE(on)}$	Base-Emitter On Voltage	0.6	0.72	V	V_{CE} = 5 V I_C = 2 mA
hfe	AC Current Gain	60		-	V_{CE}=5V, I_C=2mA, f = 1 kHz
Cob	Collector Output Capacitance		6	pF	V_{CB} = 10 V, f = 1.0 MHz
NF	Noise Figure		10	dB	V_{CE}=5V, I_C=200uA, Rg=2Kohms f=1Khz, BW=200Hz

NOTES:

1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3. These ratings are based on a maximum junction temperature of 150 degrees C.